2SC3934G

Silicon NPN epitaxial planar type

For high-frequency wide-band low-noise amplification

■ Features

- High transition frequency f_T
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Package

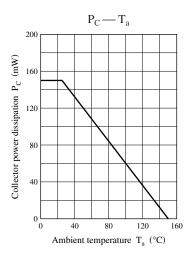
- Code SMini3-F2
- Marking Symbo

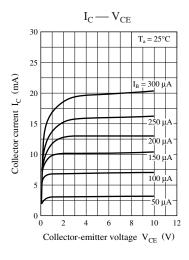
■ Absolute Maximum Ratings $T_a = 25$ °C

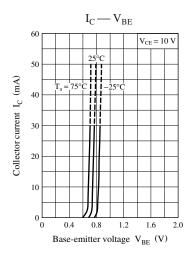
 S-Mini type package, allowing do automatic insertion through the typacking Absolute Maximum Ratings 	• Ma • Pin 1.1 2.1	lini3-F2 rking S Name Base Emitter Collecto	ymb o	10								
Parameter	Symbol	Rating	Unit	al of our s	140)						
Collector-base voltage (Emitter open)	V _{CBO}	15	V	× 00 0	SO		S.					
Collector-emitter voltage (Base open)	V _{CEO}	12	V	10, 1/2)	ردير وال)					
Emitter-base voltage (Collector open)	V_{EBO}	2.5	6.V	S. Co	(
Collector current	I_C	30	mA	70	S							
Peak collector current	I_{CP}	20	(diA)	O.	yle -							
Collector power dissipation	P _C	×0150 Q	mW	٠								
Junction temperature	T _j	150	· Co	On								
Storage temperature	Tsig	-55 to +150	o °C	a CX								
■ Electrical Characteristics T > 25°C + 3°C												
Parameter, O	Symbo		Conditio	ns	Min	Тур	Max					

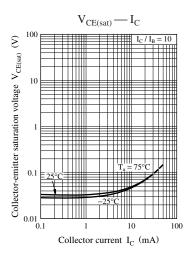
Parameter, 0	Symbol	700	conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 1$	$V, I_E = 0$			100	nA
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 2$	$V, I_C = 0$			1	μΑ
Forward current transfer ratio	$h_{\rm FE}$	$\mathbf{V}_{\mathrm{CE}} = 1$	$0 \text{ V}, I_{\text{C}} = 10 \text{ mA}$	40			_
Transition frequency	f _T O	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 10 \text{ mA}, f = 0.8 \text{ GHz}$		4.5		GHz
Collector output capacitance	Cob	$V_{CB} = 1$	$0 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			1.2	pF
(Common base, input open circuited)	O.						
Forward transfer gain	$ S_{21e} ^2$	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 20 \text{ mA}, f = 0.8 \text{ GHz}$	9	12		dB
Maximum unilateral power gain	G_{UM}	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 20 \text{ mA}, f = 0.8 \text{ GHz}$	12	14		dB
Noise figure	NF	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 5 \text{ mA}, f = 0.8 \text{ GHz}$		1.3	2.5	dB

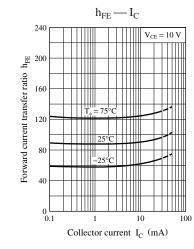
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

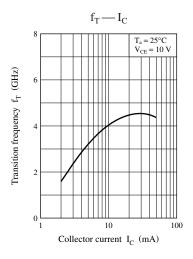


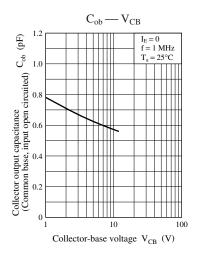


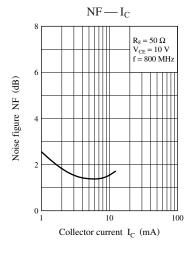


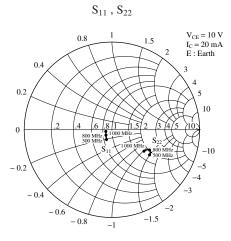




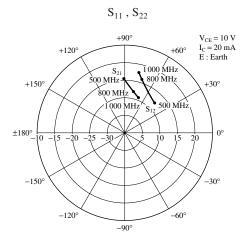






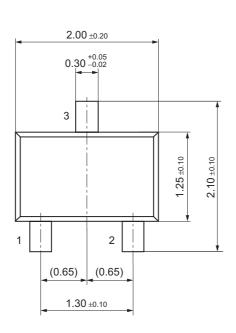


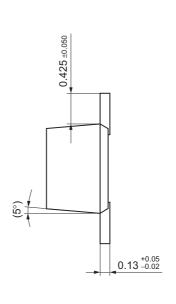
2 SJC00360AED

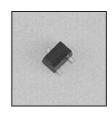


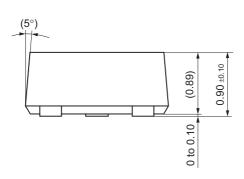
SJC00360AED 3

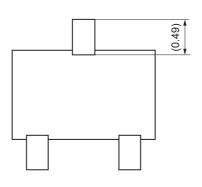
SMini3-F2 Unit: mm











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